

## Product Features

- 2400 ~ 2500MHz (ISM band)
- 110W CW Psat @ 50V
- 71% Drain Efficiency @ 50V
- Excellent Ruggedness
- Excellent Thermal Stability
- Internally Matched

## Applications

- Industrial Heating and Drying
- Scientific
- Medical : Skin Treatment, Blood Therapy
- Plasma Lighting



Package Type : NS-AS01

## Description

The 100W CW RF Power Transistor is designed for Industrial, Scientific, Medical (ISM) and Plasma Lighting applications at 2450MHz. This device is suitable for use in CW, pulse and linear applications. This high efficiency rugged device is targeted to replace Industrial magnetrons and other vacuum tubes currently powering industrial heating, drying, plasma lighting and medical systems.

## Typical CW Peak Power Performance ( $V_{DS}=+50V$ , $T_c=25^{\circ}C$ , $50\Omega$ )

Frequency [MHz]	Signal Type	Pin [W]	Power Gain [dB]	Drain Efficiency [%]	Pout [W]
2400.0	CW	4.0	15.0	73.3	127.3
2450.0		3.9	14.8	72.0	118.6
2500.0		3.8	14.6	71.0	110.3

## Absolute Maximum Ratings

Rating	Symbol	Value	Unit	Condition
Drain to Source Voltage	$V_{DSS}$	150	V	$T_c=25^{\circ}C$
Gate to Source Voltage	$V_{GS}$	-10, +2	V	$T_c=25^{\circ}C$
Operating Voltage	$V_{DD}$	52	$V_{DC}$	-
Maximum Forward Gate Current	$I_{GMAX}$	16	mA	$T_c=25^{\circ}C$
Maximum Drain Current <sup>*1</sup>	$I_{DMAX}$	6	A	$T_c=25^{\circ}C$
Power Dissipation	$P_{DISS}$	61.5	W	$T_c=85^{\circ}C$
Storage Temperature	$T_{STG}$	-65, +150	$^{\circ}C$	-
Case Operating Temperature	$T_C$	-40, +150	$^{\circ}C$	-
Operating Junction Temperature <sup>*2</sup>	$T_J$	225	$^{\circ}C$	-
Soldering Temperature <sup>*3</sup>	$T_S$	245	$^{\circ}C$	-

### Note

\*1 Current Limit for long term, reliable operation.

\*2 Continuous use at maximum temperature will affect MTTF.

\*3 Refer to the Application Note(AN-002) on soldering - "Solder Condition for RFHIC's GaN Device"

## Thermal Characteristics

Rating	Symbol	Value	Unit	Condition
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.27 <sup>*1</sup>	$^{\circ}C/W$	$T_c=85^{\circ}C$

### Note

\*1 Measured for the IE24100P at dissipation power is 61.5W

**Electrical Characteristics** (Tc=25°C unless otherwise noted)

Characteristics	Conditions	Symbol	Min	Typ	Max	Unit
DC Characteristics <sup>*1</sup>						
Gate Threshold Voltage	V <sub>DS</sub> = 10V	V <sub>GS(TH)</sub>	-3.8	-3.0	-2.3	V <sub>DC</sub>
	I <sub>D</sub> = 14.4mA					
Gate Quiescent Voltage	V <sub>DS</sub> = 50V	V <sub>GS(Q)</sub>	-	-3.1	-	V <sub>DC</sub>
	I <sub>D</sub> = 50mA					
Saturated Drain Current <sup>*2</sup>	V <sub>DS</sub> = 6V	I <sub>DS</sub>	12.0	14.4	-	A
	V <sub>GS</sub> = 2V					
Drain-Source Breakdown Voltage	V <sub>GS</sub> = -8V	V <sub>BR</sub>	150	-	-	V
	I <sub>D</sub> = 14.4mA					
Gate Leakage Current	V <sub>GS</sub> = -8V	I <sub>GLKG</sub>	-3.2	-	-	mA
	V <sub>DS</sub> = 120V					
Drain Leakage Current	V <sub>GS</sub> = -8V	I <sub>DLKG</sub>	-	-	5.8	mA
	V <sub>DS</sub> = 120V					
RF Characteristics (Fc = 2450MHz unless otherwise noted)						
Saturated Output Power <sup>*3</sup>	V <sub>DS</sub> = 50V	P <sub>SAT</sub>	100	110	-	W
	I <sub>DQ</sub> = 50mA					
CW Drain Efficiency <sup>*3</sup>	V <sub>DS</sub> = 50V	η	68	72	-	%
	I <sub>DQ</sub> = 50mA					
	P <sub>OUT</sub> = P <sub>SAT</sub> CW					
Output Mismatch Stress <sup>*4, 5</sup>	V <sub>DS</sub> = 50V	VSWR	-	-	10:1	ψ
	I <sub>DQ</sub> = 50mA					
	P <sub>OUT</sub> = P <sub>SAT</sub> Pulsed					

**Note**

\*1 Measured on wafer prior to packaging.

\*2 Scaled from PCM data.

\*3 CW(Continuous Wave) signal operation condition.

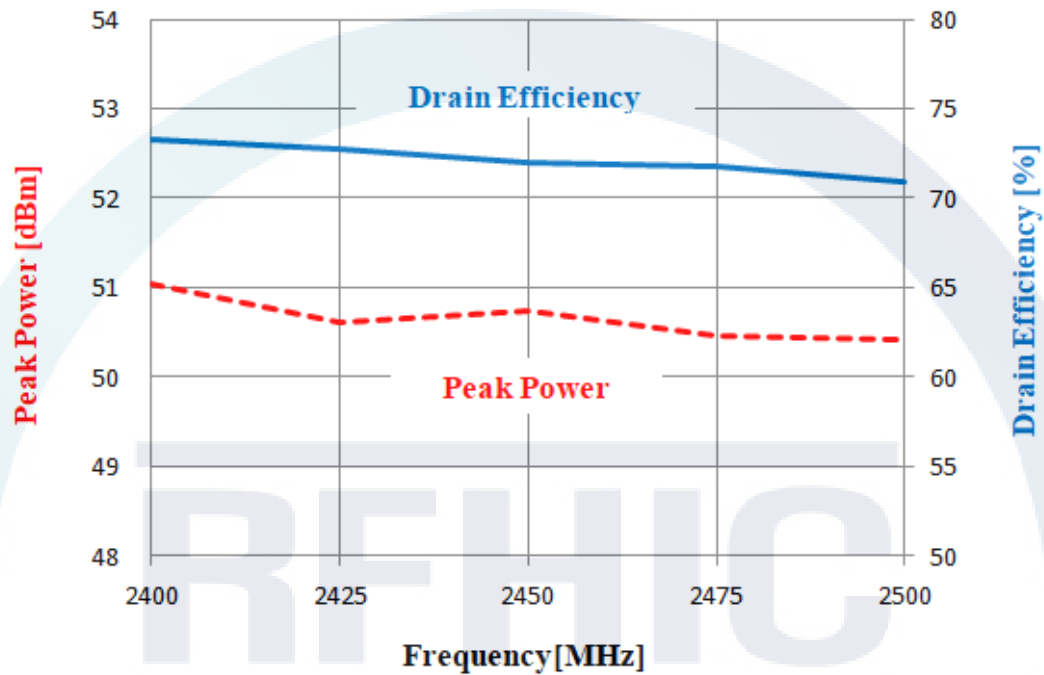
\*4 Pulse width 100usec, Duty Cycle 10%.

\*5 Measured in the IE24100P-2450MHz test board amplifier circuit, No damage at all phase angles.

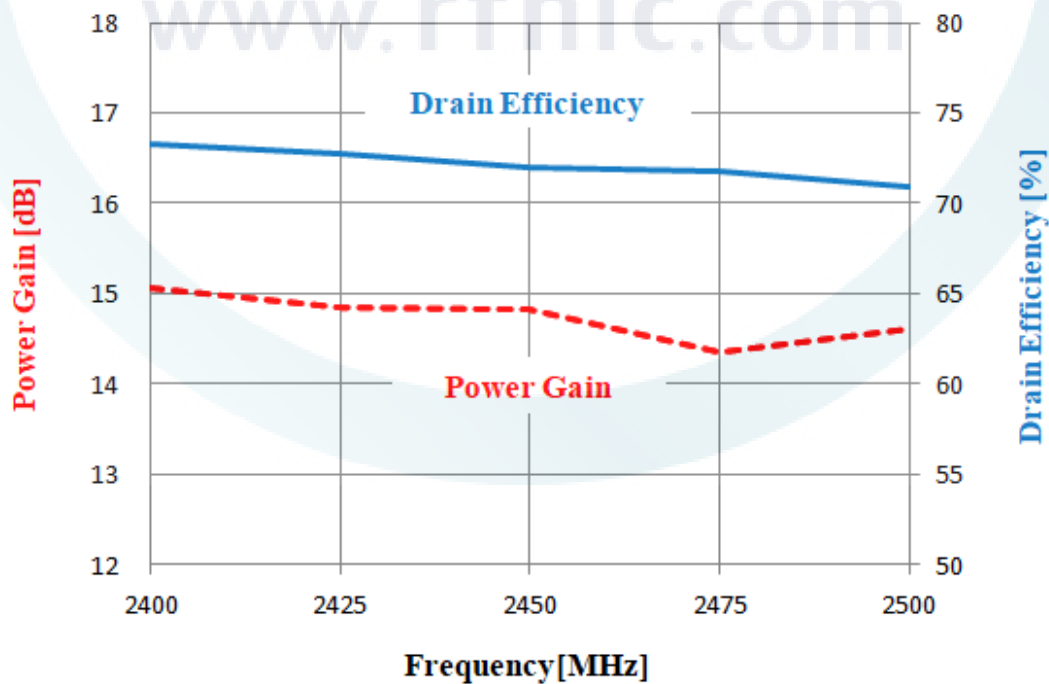
## Typical CW Performance Charts

\* Bias condition ( $I_{DQ}=50\text{mA}$  @  $V_{DS}=50\text{V}$ ,  $T_c=25^\circ\text{C}$ )

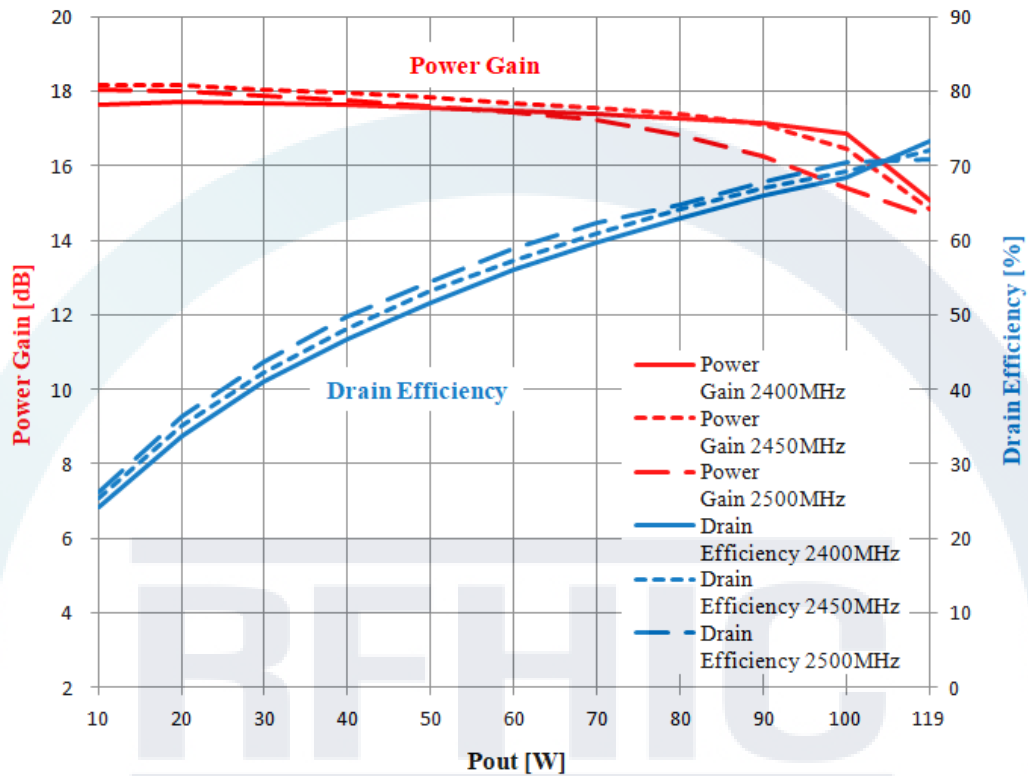
Peak Power, Drain Efficiency vs. Frequency



Power Gain, Drain Efficiency vs. Frequency

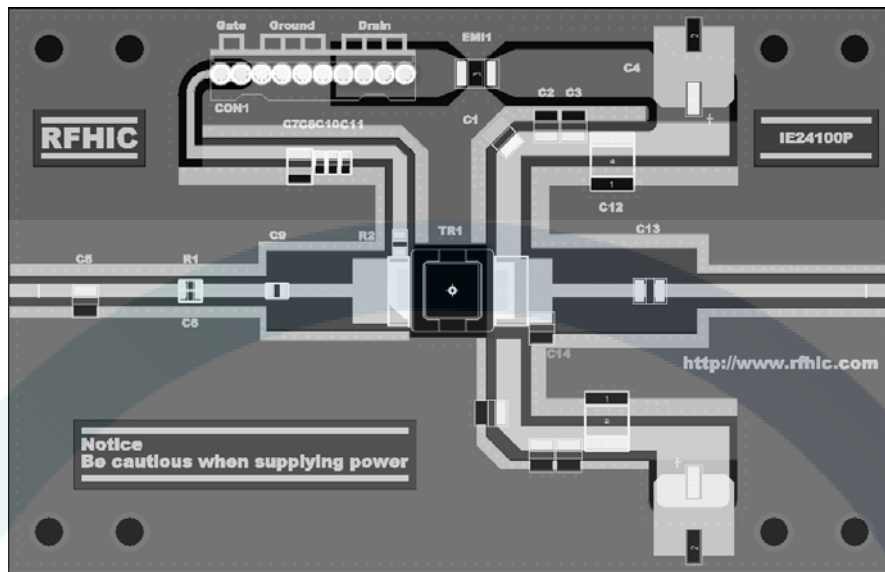


Power Gain, Drain Efficiency vs. Output Power



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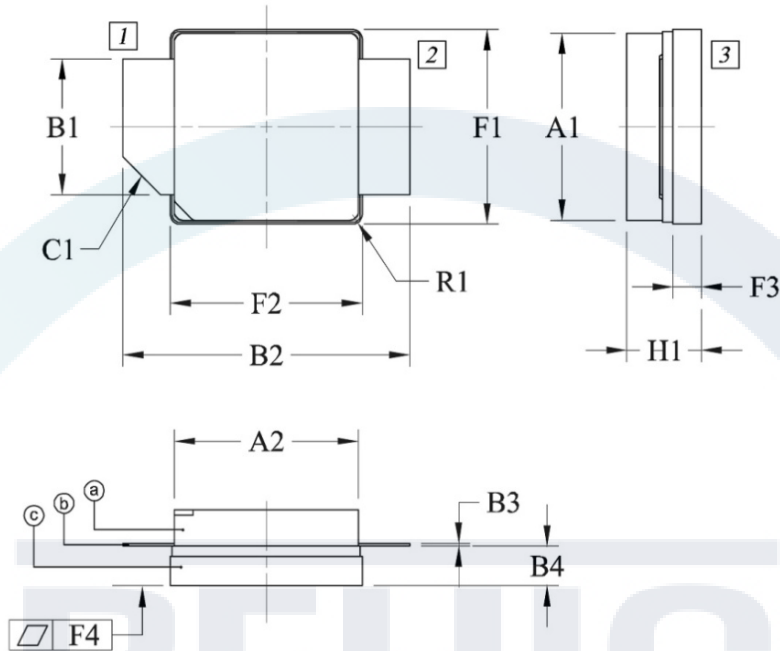
## Application Circuit



## Part List

Part	Description	Part Number	Manufacturer
R1	10 Ohm Chip Resistor, 1608	MCR03EZPJ100	ROHM
R2	20 Ohm Chip Resistor, 2012	MCR10EZJH200	ROHM
C1	2.2uF, 100V MLCC	GRM32ER72A225KA35L	MURATA
C2	10pF High Q Capacitor	501CHB100JSLE	TEMEX
C3	100pF High Q Capacitor	501CHB101JSLE	TEMEX
C4	33uF Aluminum Capacitor	BDS100VC33MJ10TP	SAMYOUNG
C5, C14	1pF High Q Capacitor	501CHB1R0BSLE	TEMEX
C6	10pF High Q Capacitor	201CHB100JSLE	TEMEX
C7	10uF, 16V MLCC	C3216X7R1C106K	TDK
C8	1nF Chip Capacitor	GRM188R71H102KA01D	MURATA
C9	1.5pF High Q Capacitor	201CHA1R5BSLE	TEMEX
C10	100pF Chip Capacitor	GRM1885C1H101JA01D	MURATA
C11	10pF Chip Capacitor	GRM1885C1H100JA01D	MURATA
C12	10uF, 100V MLCC	RS80R2A106M	MARUWA
C13	0.9pF High Q Capacitor	501CHB0R9BSLE	TEMEX
EMI1	EMI FILTER	CTH32R102S20A-TM	MARUWA
CON1	DC Connector	22-04-1101	MOLEX
PCB	$\epsilon_r=3.5 \pm 0.05$ , 0.030" (0.762mm)	RF-35TC	TACONIC.
TR1	100W GaN Transistor	IE24100P	RFHIC

## Package Dimensions (Type : NS-AS01)

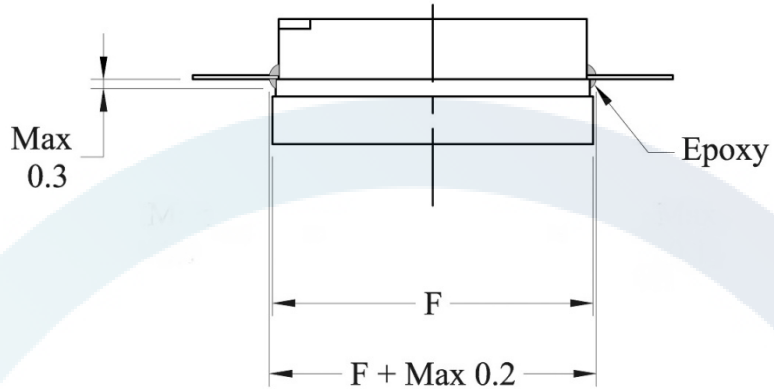
\* Unit: mm[inch] | Tolerance  $\pm 0.15$  [.006]

Pin Description		Dim.	INCH			MILLIMETER		
Pin No	Function		MIN	TYP	MAX	MIN	TYP	MAX
1	Gate	A1	.380	.384	.390	9.65	9.75	9.90
2	Drain	A2	.380	.384	.390	9.65	9.75	9.90
3	Source	B1	.274	.280	.285	6.97	7.10	7.23
		B2	.579	.598	.618	14.70	15.20	15.70
		B3	.004	.005	.007	0.10	0.13	0.18
		B4	.080	.085	.090	2.03	2.15	2.28
		C1 (Chamfer)	.075	.079	.083	1.90	2.00	2.10
		F1	.395	.400	.405	10.03	10.16	10.29
		F2	.395	.400	.405	10.03	10.16	10.29
		F3	.054	.059	.064	1.37	1.50	1.63
		F4	-	.001	-	-	0.03	-
		H1	.148	.159	.167	3.75	4.05	4.25
		L1	-	-	-	-	-	-
		L2	-	-	-	-	-	-
		R1 (Radius)	.016	.020	.024	0.40	0.50	0.60

①- Lid

②- Lead Frame

③- Flange

**Sealing Epoxy Tolerance (Type : NS-AS01)****Note**

Unit : mm

F is maximum size of flange

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**Revision History**

Part Number	Release Date	Version	Description	Data Sheet Status
IE24100P	April, 2017	0.1	Initial Release of DataSheet	Preliminary
IE24100P	October, 2017	1.0	Revision : Update Test Data	Final



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